

## **isc Silicon NPN Power Transistors**

# 2SD1064

### DESCRIPTION

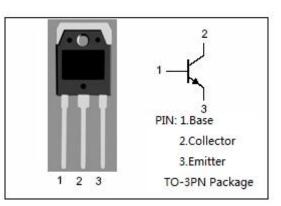
- Low Collector Saturation Voltage : V<sub>CE(sat)</sub>= 0.4V(Max)@ I<sub>C</sub>= 6A
- Wide Area of Safe Operation
- Complement to Type 2SB828
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

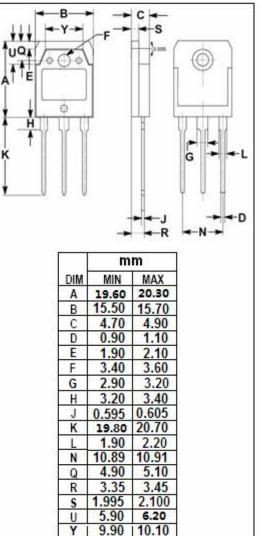
## **APPLICATIONS**

• Designed for relay drivers , high-speed inverters, converters, and other general high-current switching applications.

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
Ι <sub>C</sub>	Collector Current-Continuous	12	А
I <sub>CP</sub>	Collector Current-Pulse	17	А
Pc	Collector Power Dissipation @ T <sub>c</sub> =25°C	80	W
TJ	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)





isc website: www.iscsemi.com

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## **ELECTRICAL CHARACTERISTICS**

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1mA; R <sub>BE</sub> = ∞	50			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	60			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	6			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 0.3A			0.4	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 40V; I <sub>E</sub> = 0			100	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> =0			100	μA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 2V	70		280	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 2V	30			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V		10		MHz

Switching times

t <sub>on</sub>	Turn-on Time		0.1	μ
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 5A; I <sub>B1</sub> = I <sub>B2</sub> = 0.5A R <sub>L</sub> = 4 Ω ;P <sub>W</sub> =20 μ s; V <sub>CC</sub> = 20V	1.2	μ <b>S</b>
t <sub>f</sub>	Fall Time		0.05	μs

### h<sub>FE-1</sub> Classifications

Q	R	S
70-140	100-200	140-280

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